This GIDEP PCN is to announce specifications change with the datasheet parameters for the following International Rectifier Part No. Note that this change is related to part specification only, and not due to a die physical change.

IRH9150
-100V, P-Channel TID Hardened MOSFET in a TO-204AE package

ELECTRICAL CHARACTERISTICS @ Tj = 25°C

RDS(on) [Static Drain-to-Source On-State Resistance]
- change max limit with ID = -14A from 0.075Ω to 0.080Ω.
- change max limit with ID = -22A from 0.080Ω to 0.085Ω.

tr [Rise Time], change max limit from 150ns to 170ns.

td(off) [Turn-Off Delay Time], change max limit from 100ns to 190ns.

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

trr [Reverse Recovery Time], change max limit from 250ns to 300ns.

ELECTRICAL CHARACTERISTICS @ Tj = 25°C, Post Total Dose Irradiation

R0S(on) [Static Drain-to-Source On-State Resistance]
- change max limit at 100K Rads (Si) from 0.075Ω to 0.080Ω.
- change max limit at 300K Rads (Si) from 0.085Ω to 0.080Ω.

Reference Datasheet PD-90879